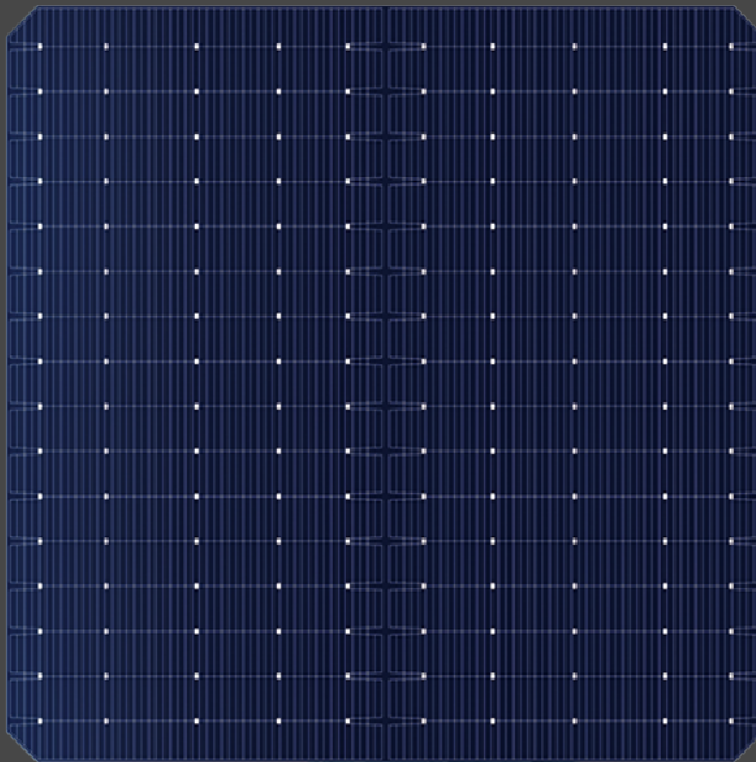




DATASHEET



LX183-N 16BB



Extremely low light-induced degradation



Strong low-light response



Low temperature poly-Si deposition process



Advanced Laser-enhanced contact optimization



Extremely low light-induced degradation



High module sealed power



Advanced passivation& doping technology



Strong weather resistance



Extremely low light-induced degradation

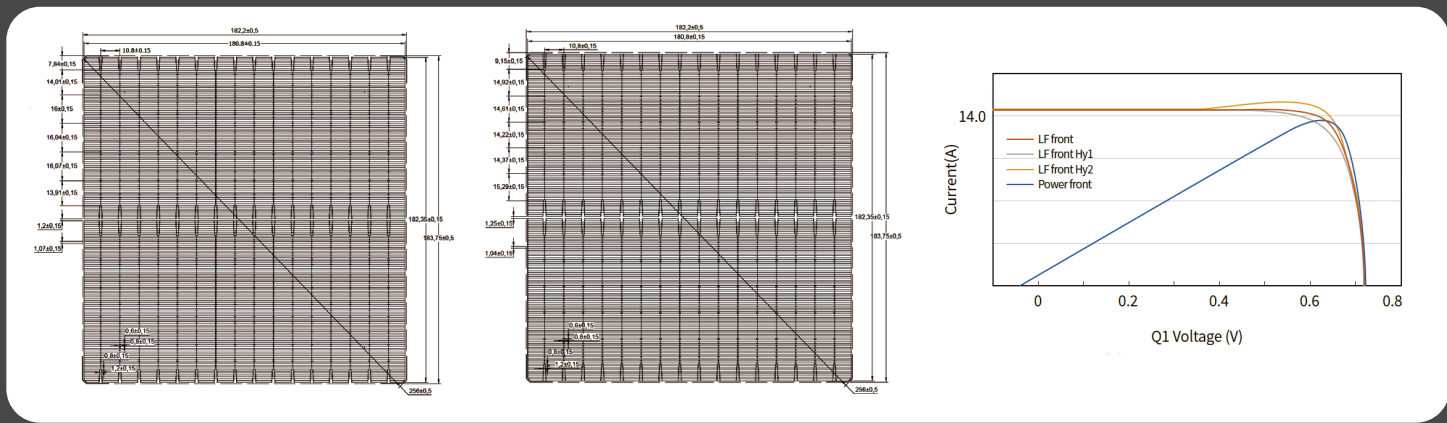
TECHNICAL CHARACTERISTICS

Dimension	182.2mm*183.75mm±0.5mm Φ256±0.5mm	TkVoltage:-0.25%/K
Thickness	130um±13um	TkCurrent:0.045%/K
Front	16*0.05±0.035mm bus bars(silver) black anti-reflecting coating (silicon nitride)	TkPower:-0.30%/K
Back(+)	0.05±0.035mm bus bars(silver) black anti-reflecting coating (silicon nitride)	Rsh≥50Ω,Irev2≤0.5A

LIGHT INTENSITY AND RELIABILITY

Intensity(W/m²)	Voc	Isc
1000	1.000	1.000
900	0.996	0.903
800	0.991	0.803
600	0.988	0.602
400	0.962	0.403

The Voc(Isc) tested by 1000W/m2 is the standard, and the Voc(Isc) decreases with the strong decrease in light.



WELDABILITY Minimum peeling intensity ≥0.5N/mm Results may vary depending on the welding ribbon, welding methods and conditions.

ELECTRICAL CHARACTERISTICS

Eff(%)	Pmpp(W)	Vmpp(V)	Ippp(A)	Voc(V)	Isc(A)	FF(%)
26.0	8.70	0.639	13.62	0.738	14.11	83.57
25.9	8.67	0.638	13.59	0.737	14.09	83.48
25.8	8.64	0.637	13.56	0.736	14.08	83.33
25.7	8.60	0.636	13.53	0.735	14.06	83.24
25.6	8.57	0.635	13.49	0.734	14.05	83.09
25.5	8.54	0.633	13.48	0.732	14.04	83.07
25.4	8.50	0.632	13.45	0.731	14.03	82.90
25.3	8.47	0.631	13.41	0.730	14.01	82.75
25.2	8.43	0.630	13.38	0.730	14.00	82.60
25.1	8.40	0.629	13.36	0.729	13.99	82.40
25.0	8.37	0.626	13.36	0.727	13.98	82.32
24.9	8.33	0.624	13.35	0.726	13.97	82.19
24.8	8.30	0.621	13.36	0.725	13.96	82.03
24.7	8.27	0.620	13.33	0.724	13.95	81.86
24.6	8.23	0.618	13.32	0.723	13.94	81.70
24.5	8.20	0.616	13.31	0.721	13.93	81.65
24.4	8.17	0.615	13.28	0.719	13.9	81.66
24.3	8.13	0.614	13.25	0.718	13.89	81.55
24.2	8.10	0.613	13.21	0.717	13.88	81.39
24.1	8.07	0.612	13.18	0.716	13.87	81.23